

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: SUD23N06-31L-T4-E3

Manufacturer: Vishay Siliconix

Package: Please confirm with sales

Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/vishay-siliconix/sud23n06-31l-t4-e3.html>

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Contact Information

Email: info@antrexco.com

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Supplier verification and packaging condition review

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Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

N-Channel 60 V (D-S), 175 °C MOSFET, Logic Level

PRODUCT SUMMARY

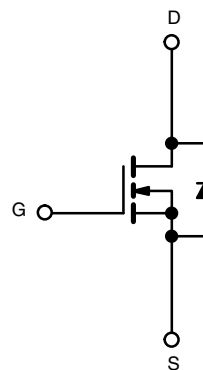
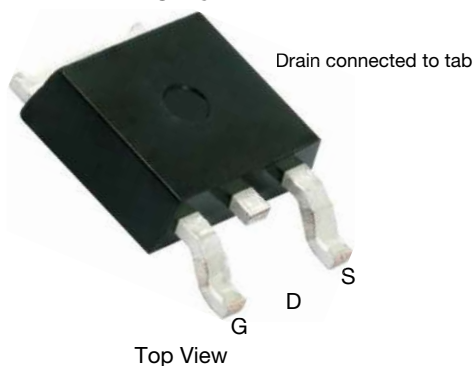
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_d (A) ^a
60	0.031 at $V_{GS} = 10$ V	23
	0.045 at $V_{GS} = 4.5$ V	19.5

FEATURES

- TrenchFET® power MOSFET
- 175 °C junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

TO-252



N-Channel MOSFET

Ordering Information:

SUD23N06-31L-E3 (lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175$ °C) ^b	$T_C = 25$ °C	I_D	23	A
	$T_C = 100$ °C		16.5	
Pulsed Drain Current		I_{DM}	50	
Continuous Source Current (Diode Conduction)		I_S	23	
Avalanche Current		I_{AS}	20	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	$L = 0.1$ mH	E_{AS}	20	mJ
Maximum Power Dissipation	$T_C = 25$ °C	P_D	37.5	W
	$T_A = 25$ °C		3 ^a	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient ^a	$t \leq 10$ s	R_{thJA}	18	22	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	3.2	4	

Note

a. Surface mounted on 1" x 1" FR4 board.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. ^a	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1	2	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C	-	-	50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50	-	-	A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A	-	0.025	0.031	Ω
		V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C	-	-	0.055	
		V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C	-	-	0.069	
		V _{GS} = 4.5 V, I _D = 10 A	-	0.037	0.045	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A	-	20	-	S
Dynamic ^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	-	670	-	pF
Output Capacitance	C _{oss}		-	140	-	
Reverse Transfer Capacitance	C _{rss}		-	60	-	
Total Gate Charge ^c	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 23 A	-	11	17	nC
Gate-Source Charge ^c	Q _{gs}		-	3	-	
Gate-Drain Charge ^c	Q _{gd}		-	3	-	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 1.3 Ω I _D ≅ 23 A, V _{GEN} = 10 V, R _g = 2.5 Ω	-	8	15	ns
Rise Time ^c	t _r		-	15	25	
Turn-Off Delay Time ^c	t _{d(off)}		-	30	45	
Fall Time ^c	t _f		-	25	40	
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C)						
Pulsed Current	I _{SM}		-	-	50	A
Diode Forward Voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V	-	1	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 15 A, dI/dt = 100 A/μs	-	30	60	ns

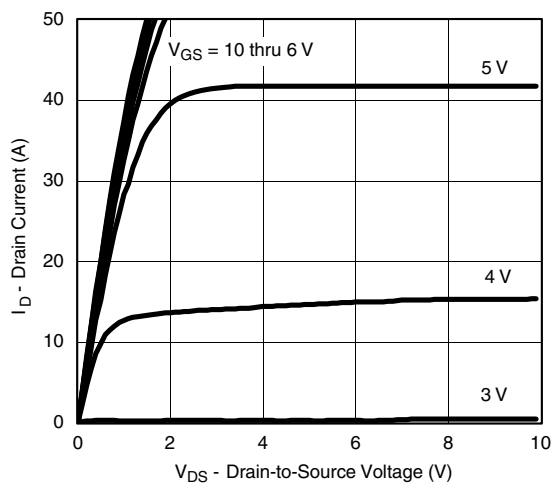
Notes

- a. For design aid only; not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
c. Independent of operating temperature.

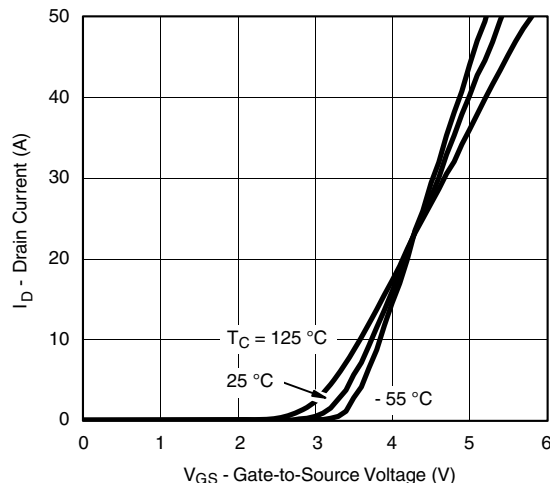
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



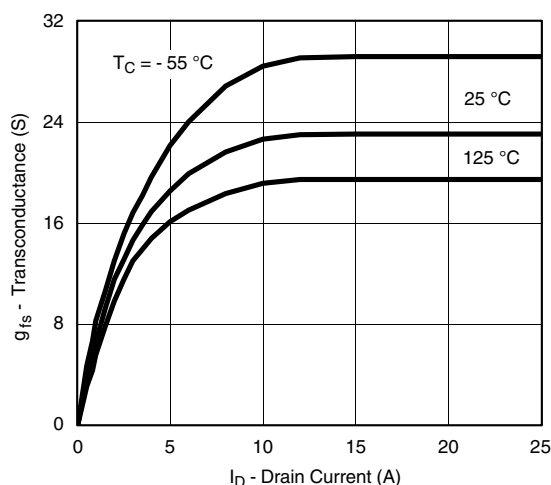
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



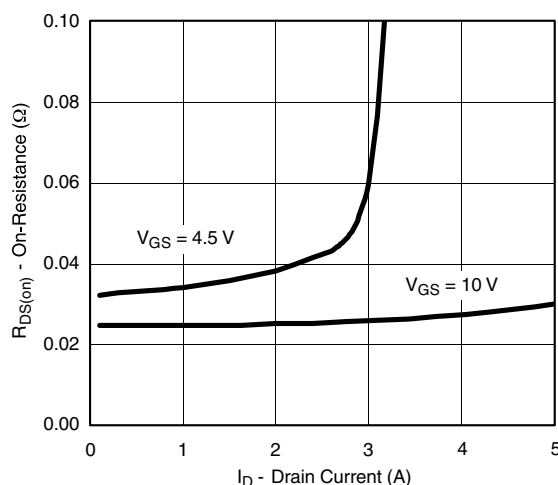
Output Characteristics



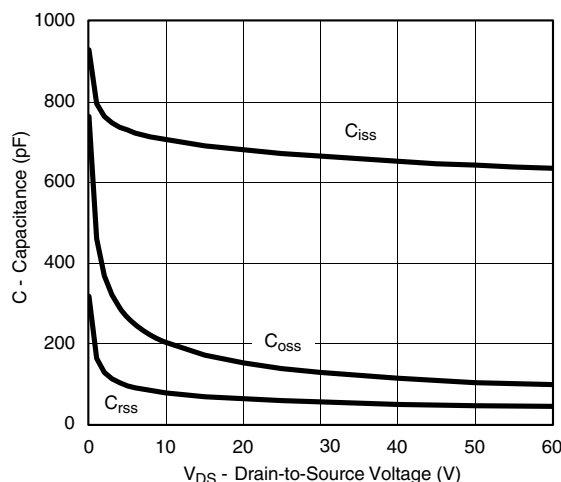
Transfer Characteristics



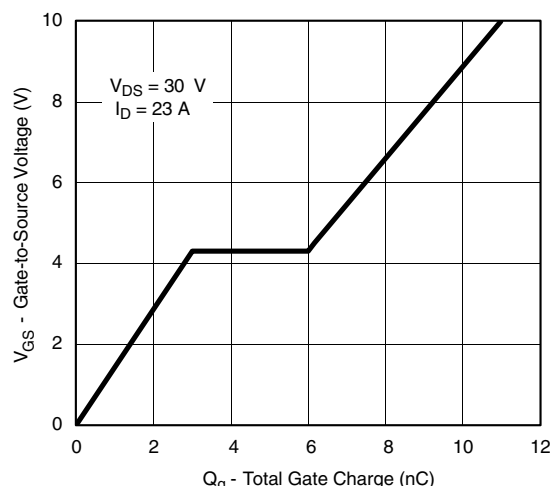
Transconductance



On-Resistance vs. Drain Current



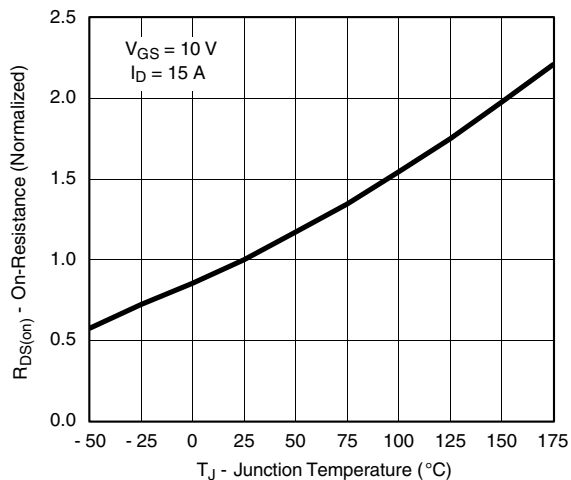
Capacitance



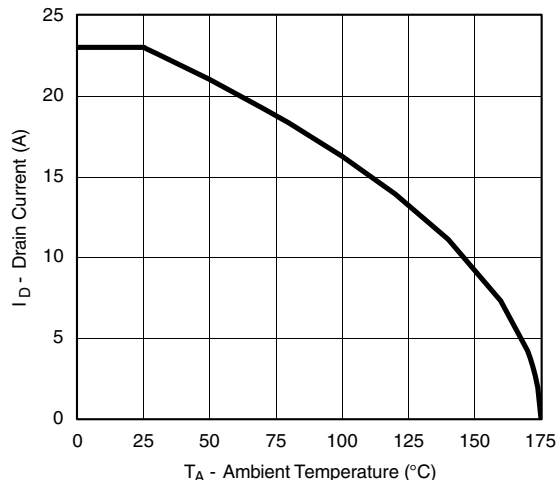
Gate Charge



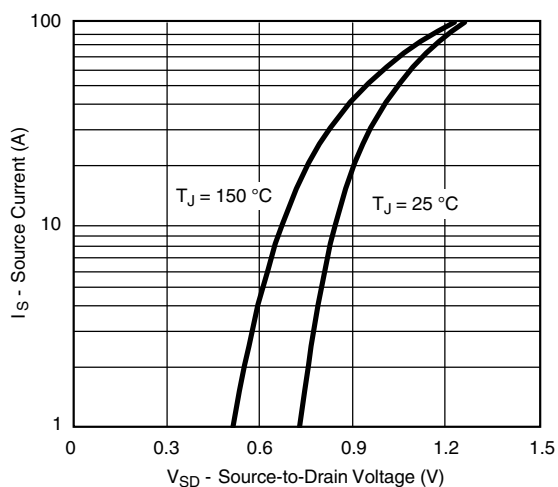
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



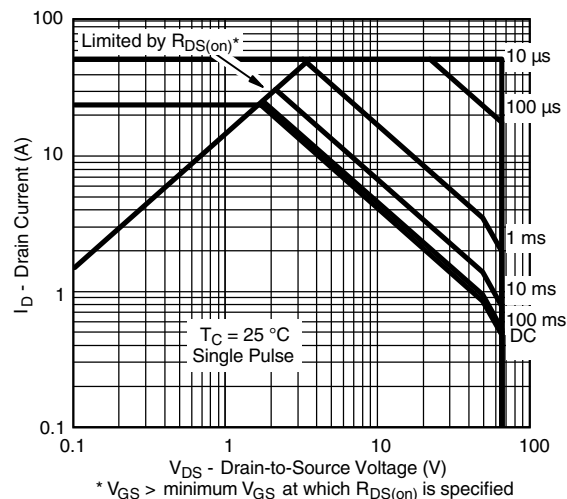
On-Resistance vs. Junction Temperature



Maximum Drain Current vs. Ambient Temperature



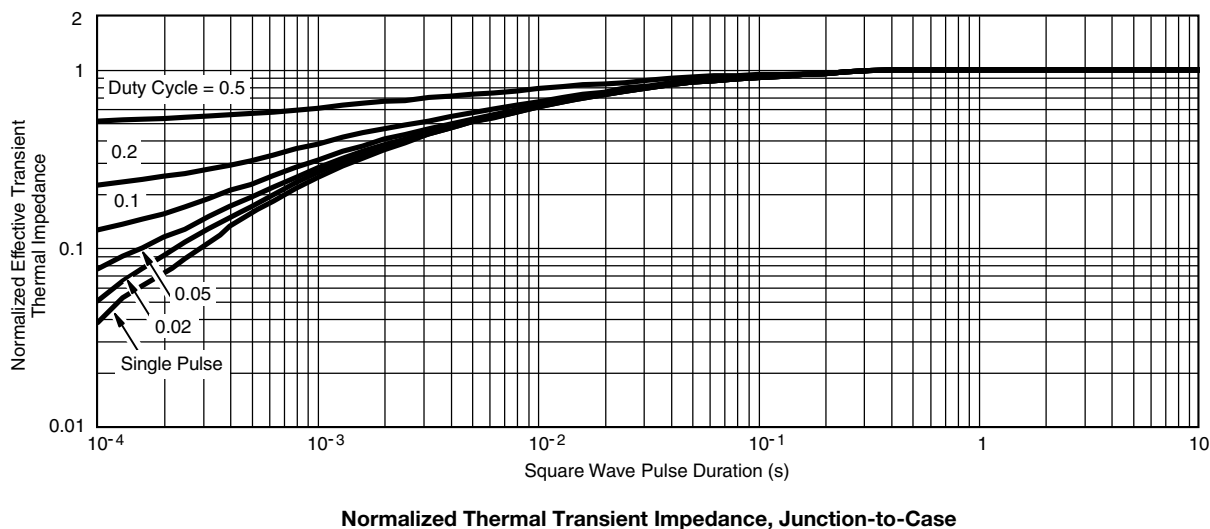
Source-Drain Diode Forward Voltage



Safe Operating Area



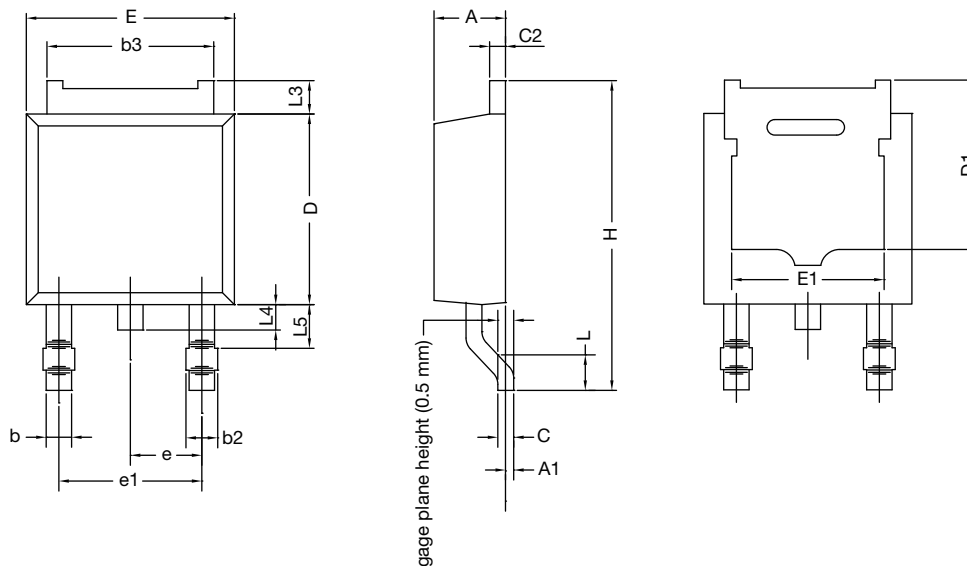
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72145.

TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



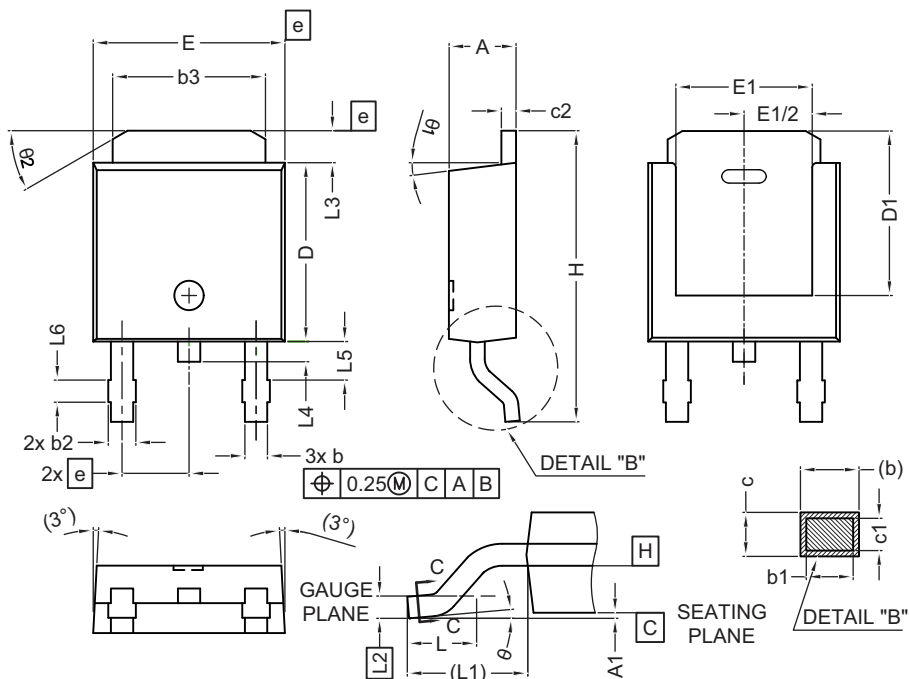
MILLIMETERS		
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

Note

- Dimension L3 is for reference only



VERSION 2: FACILITY CODE = N



DIM.	MILLIMETERS	
	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

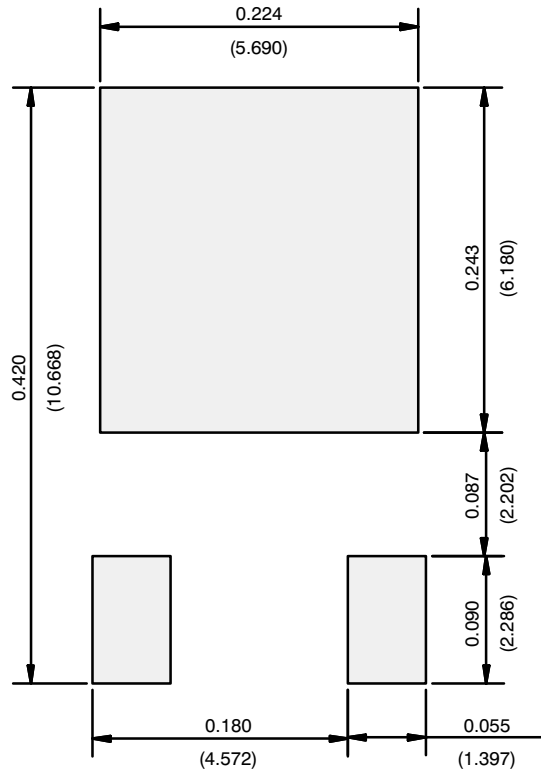
DIM.	MILLIMETERS	
	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
theta	0°	10°
theta1	0°	15°
theta2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022
DWG: 5347

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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